

Plastic-Encapsulate Transistors

DUAL TRANSISTOR (NPN+NPN)

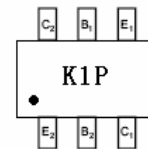
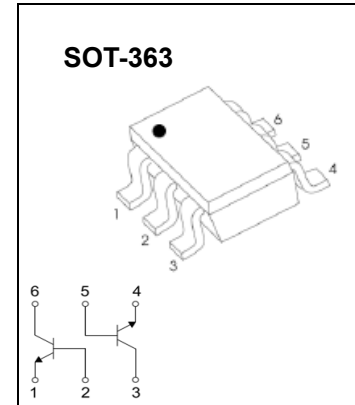
FEATURE

Complementary PNP Type available MMDT2907ADW

MARKING: K1P

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	75	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	600	mA
P_C	Collector Power Dissipation	200	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	75		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$		10	nA
Collector cut-off current	I_{CEX}	$V_{CE}=60\text{V}, V_{EB(off)}=3\text{V}$		10	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=3\text{V}, I_C=0$		10	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	35		
	$h_{FE(2)}$	$V_{CE}=10\text{V}, I_C=1\text{mA}$	50		
	$h_{FE(3)}$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	75		
	$h_{FE(4)}$	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	
	$h_{FE(5)}$	$V_{CE}=10\text{V}, I_C=500\text{mA}$	40		
	$h_{FE(6)}$	$V_{CE}=1\text{V}, I_C=150\text{mA}$	35		
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.3	V
	$V_{CE(sat)2}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C=150\text{mA}, I_B=15\text{mA}$	0.6	1.2	V
	$V_{BE(sat)2}$	$I_C=500\text{mA}, I_B=50\text{mA}$		2	V
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=20\text{mA}, f=100\text{MHz}$	300		MHz
Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		8	pF
Input Capacitance	C_{ib}	$V_{EB}=0.5\text{V}, I_C=0, f=1\text{MHz}$		25	pF
Noise Figure	NF	$V_{CE}=10\text{V}, I_C=100\mu\text{A}, f=1\text{KHz}, R_S=1\text{K}\Omega$		4	dB

Switching characteristics

Parameter	Symbol	Test conditions	Min	Max	Unit
Delay time	t_d	$V_{CC}=30\text{V}, I_C=150\text{mA}, V_{BE(off)}=0.5\text{V}, I_{B1}=15\text{mA}$		10	nS
Rise time	t_r			25	nS
Storage time	t_s	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=-I_{B2}=15\text{mA}$		225	nS
Fall time	t_f			60	nS



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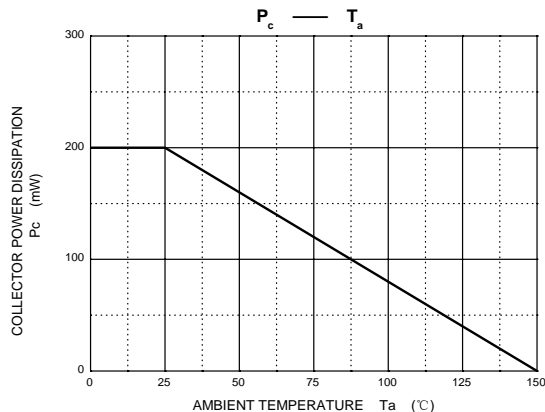
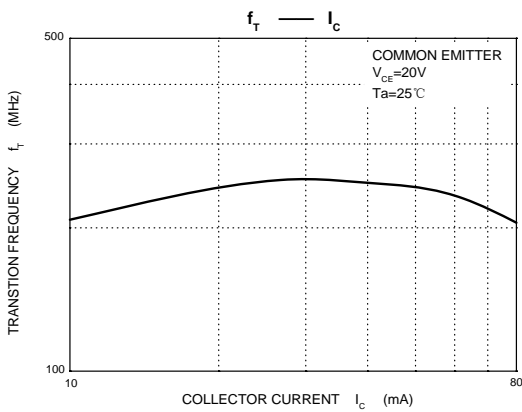
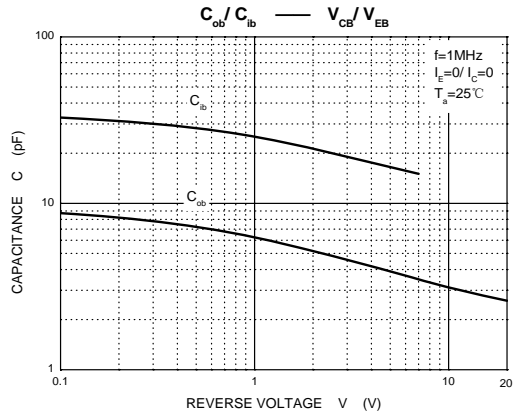
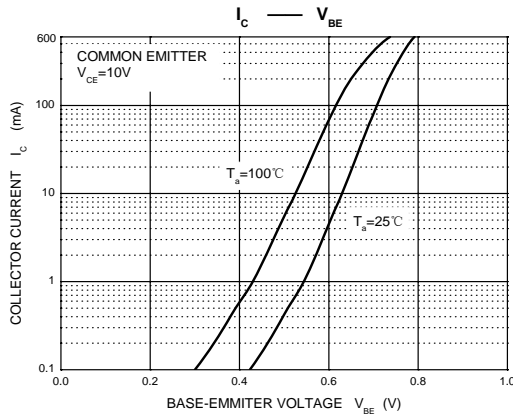
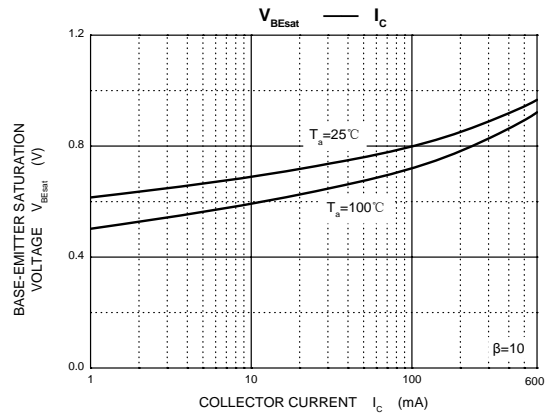
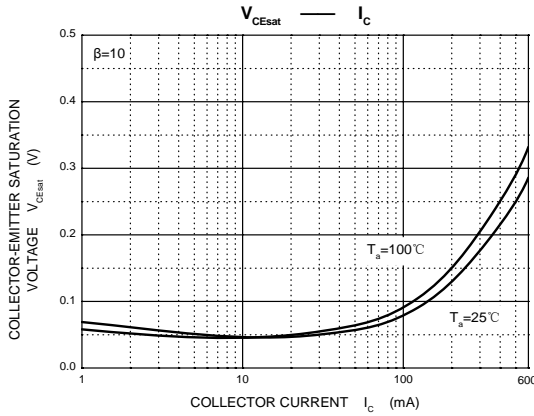
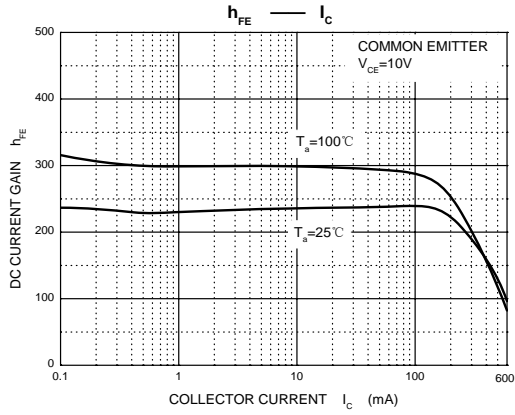
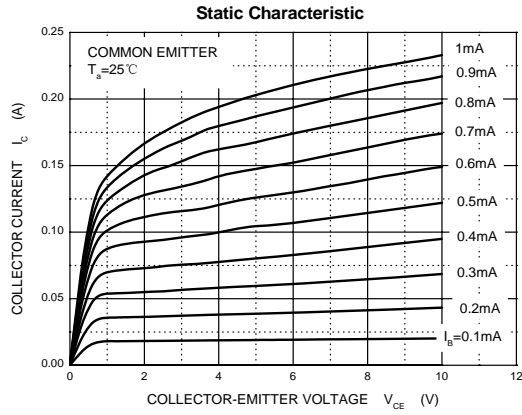
SOT-363



MMDT2222ADW

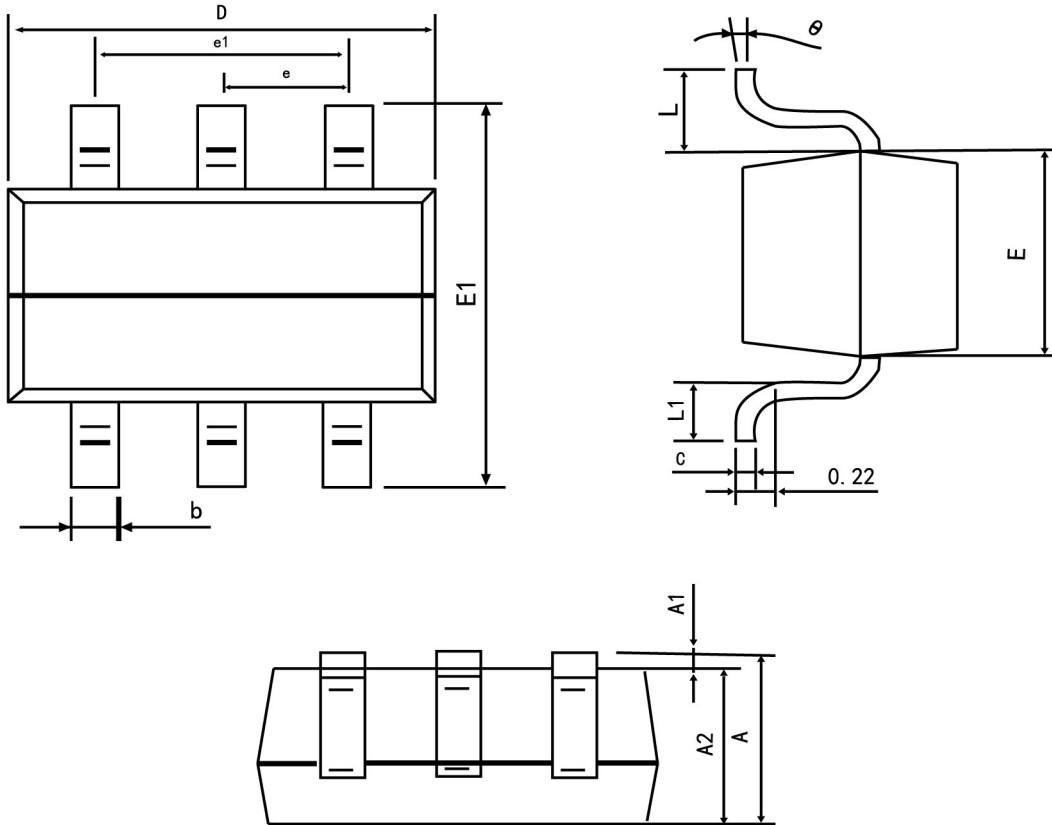
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Typical Characteristics





SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
theta	0°	8°